FUJI ELECTRIC

2SK2651-01MR

FAP-IIS Series

N-channel MOS-FET			
900V	2,5Ω	6A	50W

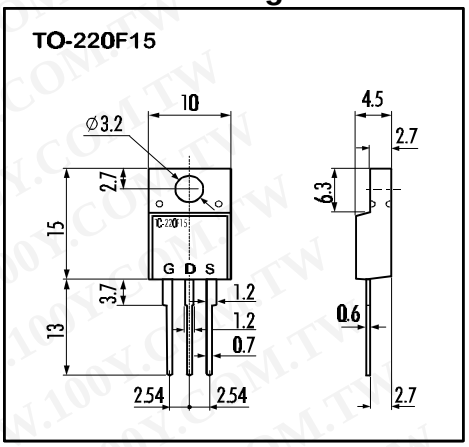
勝 特 力 材 料 886-3-5753170
胜特力电子(上海) 86-21-34970699
胜特力电子(深圳) 86-755-83298787
Http://www.100y.com.tw

> Features

- High Speed Switching
- Low On-Resistance
- No Secondary Breakdown
- Low Driving Power
- High Voltage
- VGS = ± 30V Guarantee
- Repetitive Avalanche Rated

> Outline Drawing

TO-220F15



> Applications

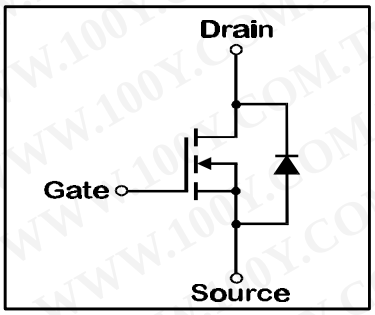
- Switching Regulators
- UPS
- DC-DC converters
- General Purpose Power Amplifier

> Maximum Ratings and Characteristics

- Absolute Maximum Ratings (T_C=25°C), unless otherwise specified

Item	Symbol	Rating	Unit
Drain-Source-Voltage	V_{DS}	900	V
Continous Drain Current	I_D	6	A
Pulsed Drain Current	$I_{D(puls)}$	24	A
Gate-Source-Voltage	V_{GS}	±30	V
Repetitive or Non-Repetitive (T_{ch} ≤ 150°C)	I_{AR}	6	A
Avalanche Energy	E_{AS}	71,9	mJ
Max. Power Dissipation	P_D	50	W
Operating and Storage Temperature Range	T_{ch}	150	°C
	T_{stg}	-55 ~ +150	°C

> Equivalent Circuit



- Electrical Characteristics (T_C=25°C), unless otherwise specified

Item	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown-Voltage	$V_{(BR)DSS}$	I_D=1mA V_{GS}=0V	900			V
Gate Threshhold Voltage	$V_{GS(th)}$	I_D=1mA V_{DS}=V_{GS}	3,5	4,0	4,5	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=900V T_{ch}=25°C		10	500	µA
		V_{GS}=0V T_{ch}=125°C		0,2	1,0	mA
Gate Source Leakage Current	I_{GSS}	V_{GS}=±30V V_{DS}=0V		10	100	nA
Drain Source On-State Resistance	$R_{DS(on)}$	I_D=3A V_{GS}=10V		1,87	2,5	Ω
Forward Transconductance	g_{fs}	I_D=3A V_{DS}=25V		4		S
Input Capacitance	C_{iss}	V_{DS}=25V		900		pF
Output Capacitance	C_{oss}	V_{GS}=0V		130		pF
Reverse Transfer Capacitance	C_{rss}	f=1MHz		70		pF
Turn-On-Time t_{on} (t_{on}=$t_{d(on)}$+t_r)	$t_{d(on)}$	V_{CC}=600V		25		ns
	t_r	I_D=6A		80		ns
Turn-Off-Time t_{off} (t_{on}=$t_{d(off)}$+t_f)	$t_{d(off)}$	V_{GS}=10V		70		ns
	t_f	R_{GS}=10 Ω		40		ns
Avalanche Capability	I_{AV}	L = 100µH T_{ch}=25°C	6			A
Diode Forward On-Voltage	V_{SD}	I_F=2xI_{DR} V_{GS}=0V T_{ch}=25°C		1,0		V
Reverse Recovery Time	t_{rr}	I_F=I_{DR} V_{GS}=0V		850		ns
Reverse Recovery Charge	Q_{rr}	-dI_F/dt=100A/µs T_{ch}=25°C		8,5		µC

- Thermal Characteristics

Item	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Thermal Resistance	$R_{th(ch-c)}$	channel to case			3,125	°C/W
	$R_{th(ch-a)}$	channel to air			62,5	°C/W

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900V	2,5Ω	6A	50W

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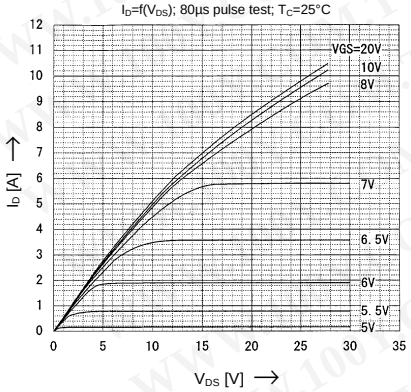
> Characteristics

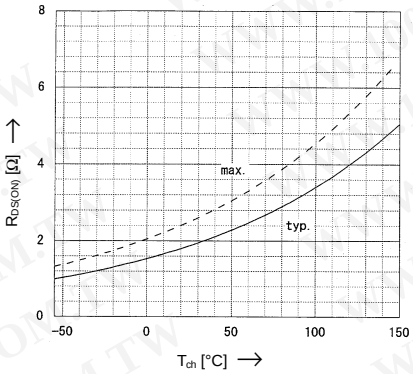
Typical Output Characteristics

$I_D=f(V_{DS})$; 80µs pulse test; $T_C=25°C$



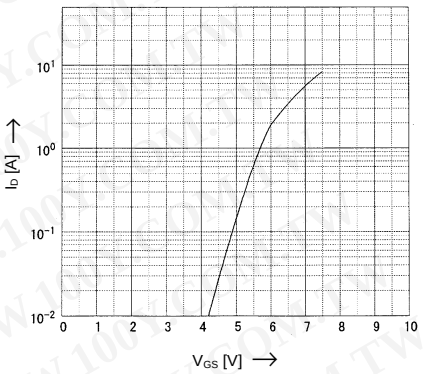
Drain-Source-On-State Resistance vs. T_{ch}

$R_{DS(on)}=f(Tch)$: $I_D=3A$; $V_{GS}=10V$



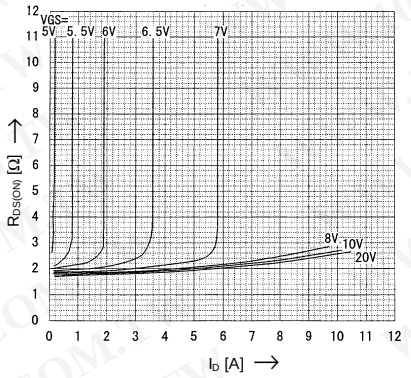
Typical Transfer Characteristics

$I_D=f(V_{GS})$; 80µs pulse test; $V_{DS}=25V$; $T_{ch}=25°C$



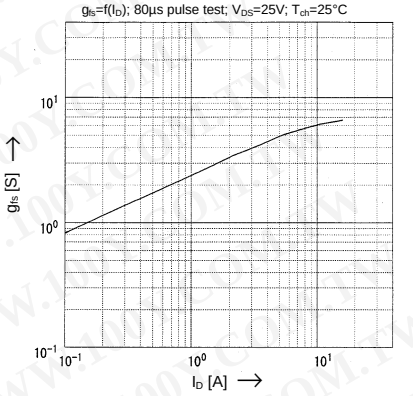
Typical Drain-Source-On-State-Resistance vs. I_D

$R_{DS(on)}=f(I_D)$; 80µs pulse test; $T_C=25°C$



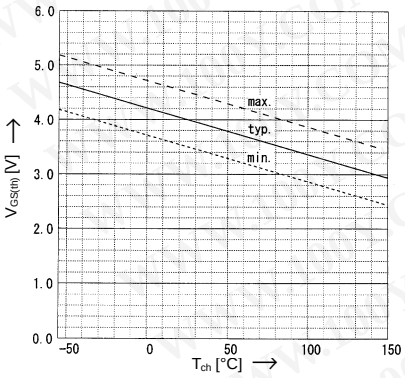
Typical Forward Transconductance vs. I_D

$g_{fs}=f(I_D)$; 80µs pulse test; $V_{DS}=25V$; $T_{ch}=25°C$



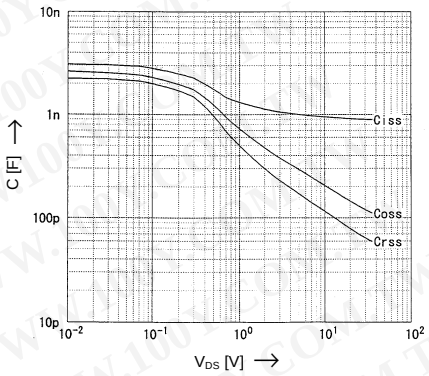
Gate Threshold Voltage vs. T_{ch}

$V_{GS(th)}=f(T_{ch})$; $I_D=1mA$; $V_{DS}=V_{GS}$



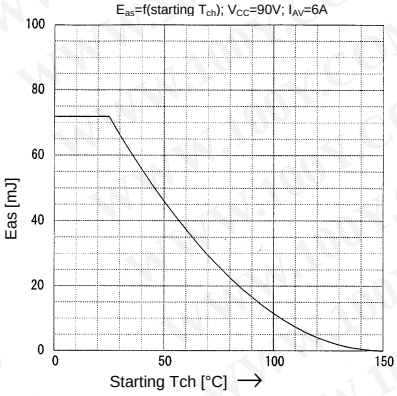
Typical Capacitances vs. V_{DS}

$C=f(V_{DS})$; $V_{GS}=0V$; $f=1MHz$



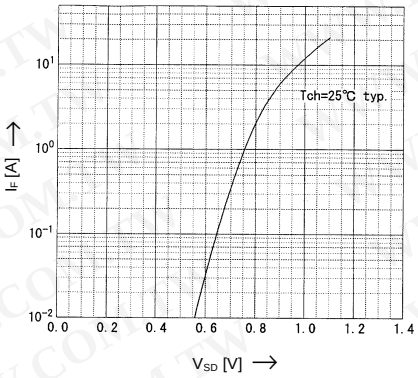
Avalanche Energy Derating

$E_{as}=f(\text{starting } T_{ch})$; $V_{CC}=90V$; $I_{AV}=6A$



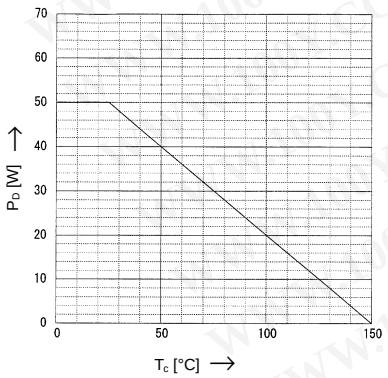
Forward Characteristics of Reverse Diode

$I_F=f(V_{SD})$; 80µs pulse test; $V_{GS}=0V$



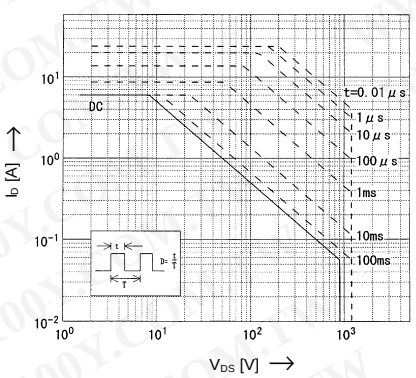
Allowable Power Dissipation vs. T_C

$P_D=f(Tc)$



Safe operation area

$I_D=f(V_{DS})$: D=0,01, Tc=25°C



Transient Thermal impedance

$Z_{thch}=f(t)$ parameter:D=t/T